SUBSTRATE PROCESSING APPARATUS, SUBSTRATE PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE AND PROGRAM

ABSTRACT

There is provided a technique capable of improving a processing uniformity between substrates. According to one aspect thereof, a substrate processing apparatus includes: a process vessel having a process region; a first nozzle having first holes, through which a first gas is supplied to substrates, arranged over the entire process region; a second nozzle having second holes, through which a second gas reacting with the first gas is supplied to the substrates, arranged over the entire process region; a third nozzle having third holes, through which an adsorption inhibitory gas inhibiting an adsorption of the first gas is supplied to the substrates, arranged corresponding to a part of the process region; and a gas supply system for supplying the first gas, the second gas and the adsorption inhibitory gas to the substrates through the first nozzle, the second nozzle and the third nozzle, respectively.

Figure 1